

HIGH SPEED 2K X 8 DUAL-PORT STATIC RAM WITH INTERRUPTS

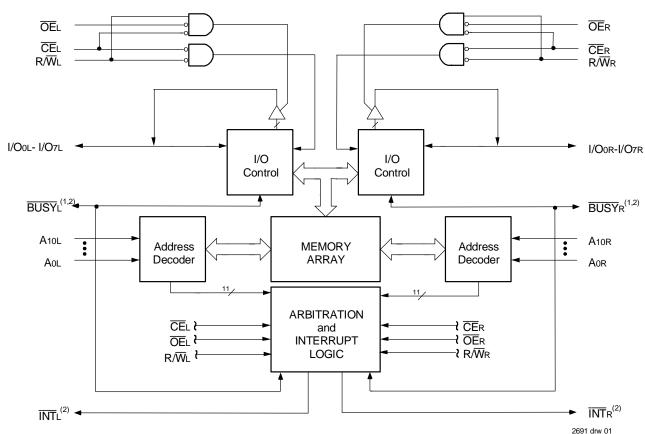
IDT71321SA/LA IDT71421SA/LA

Features

- High-speed access
 - Commercial: 20/25/35/55ns (max.)
 - Industrial: 25/55ns (max.)
- Low-power operation
 - IDT71321/IDT71421SA
 - Active: 325mW (typ.)
 - Standby: 5mW (typ.)
 - IDT71321/421LA
 - Active: 325mW (typ.)
 - Standby: 1mW (typ.)
- ◆ Two INT flags for port-to-port communications

- MASTER IDT71321 easily expands data bus width to 16-ormore-bits using SLAVE IDT71421
- On-chip port arbitration logic (IDT71321 only)
- ◆ BUSY output flag on IDT71321; BUSY input on IDT71421
- Fully asynchronous operation from either port
- Battery backup operation 2V data retention (LA only)
- ◆ TTL-compatible, single 5V ±10% power supply
- ◆ Available in 52-Pin PLCC, 64-Pin TQFP, and 64-Pin STQFP
- Industrial temperature range (-40°C to +85°C) is available for selected speeds
- Green parts available, see ordering information

Functional Block Diagram



NOTES:

- IDT71321 (MASTER): BUSY is open drain output and requires pullup resistor of 270Ω. IDT71421 (SLAVE): BUSY is input.
- 2. Open drain output: requires pullup resistor of 270Ω .

OCTOBER 2008

Description

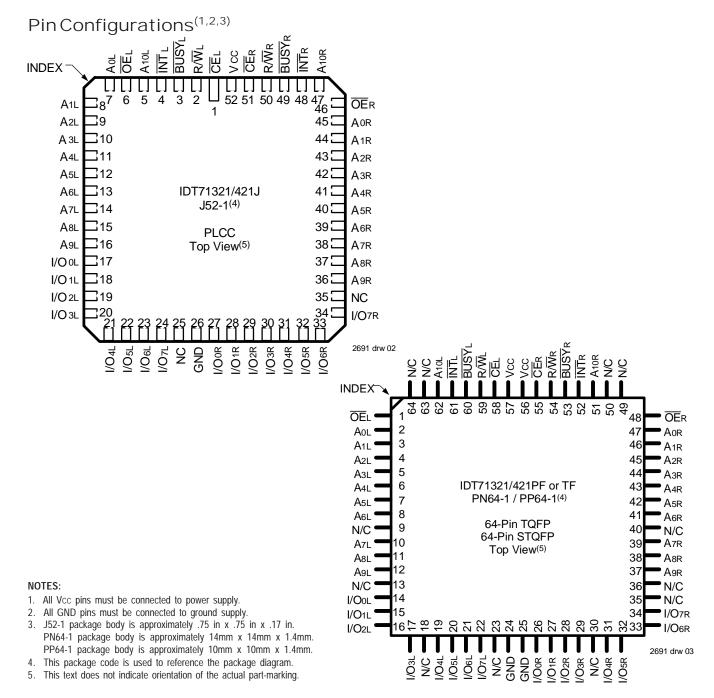
The IDT71321/IDT71421 are high-speed 2K x 8 Dual-Port Static RAMs with internal interrupt logic for interprocessor communications. The IDT71321 is designed to be used as a stand-alone 8-bit Dual-Port Static RAM or as a "MASTER" Dual-Port Static RAM together with the IDT71421 "SLAVE" Dual-Port in 16-bit-or-more word width systems. Using the IDT MASTER/SLAVE Dual-Port Static RAM approach in 16-or-more-bit memory system applications results in full speed, error-free operation without the need for additional discrete logic.

Both devices provide two independent ports with separate control,

address, and I/O pins that permit independent, asynchronous access for reads or writes to any location in memory. An automatic power down feature, controlled by $\overline{\text{CE}}$, permits the on chip circuitry of each port to enter a very low standby power mode.

Fabricated using IDT's CMOS high-performance technology, these devices typically operate on only 325mW of power. Low-power (LA) versions offer battery backup data retention capability, with each Dual-Port typically consuming 200µW from a 2V battery.

The IDT71321/IDT71421 devices are packaged in 52-pin PLCCs, 64-pin TQFPs, and 64-pin STQFPs.



Capacitance⁽¹⁾

$(TA = +25^{\circ}C, f = 1.0MHz) TQFP Only$

Symbol	Parameter	Conditions ⁽²⁾	Max.	Unit
CIN	Input Capacitance	VIN = 3dV	9	pF
Соит	Output Capacitance	Vout = 3dV	10	pF

NOTES:

 This parameter is determined by device characterization but is not production tested

2. 3dv references the interpolated capacitance when the input and output signals switch from 0V to 3V or from 3V to 0V.

Recommended Operating Temperature and Supply Voltage^(1,2)

Grade	Ambient Temperature	GND	Vcc
Commercial	0°C to +70°C	0V	5.0V <u>+</u> 10%
Industrial	-40°C to +85°C	0V	5.0V <u>+</u> 10%

2691 tbl 02

NOTES:

2691 tbl 00

- 1. This is the parameter Ta. This is the "instant on" case temperature.
- Industrial temperature: for specific speeds, packages and powers contact your sales office.

Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Commercial & Industrial	Unit			
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +7.0	٧			
TBIAS	Temperature Under Bias	-55 to +125	°C			
Tstg	Storage Temperature	-65 to +150	°C			
Іоит	DC Output Current	50	mA			

NOTES:

Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS
may cause permanent damage to the device. This is a stress rating only
and functional operation of the device at these or any other conditions
above those indicated in the operational sections of the specification is not
implied. Exposure to absolute maximum rating conditions for extended
periods may affect reliability.

2. VTERM must not exceed Vcc + 10% for more than 25% of the cycle time or 10ns maximum, and is limited to \leq 20mA for the period of VTERM \geq Vcc + 10%.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Мах.	Unit
Vcc	Supply Voltage	4.5	5.0	5.5	٧
GND	Ground	0	0	0	V
VIH	Input High Voltage	2.2		6.0(2)	V
VIL	Input Low Voltage	-0.5 ⁽¹⁾	_	0.8	V

2691 tbl 0

NOTES:

2691 tbl 01

- 1. VIL (min.) = -1.5V for pulse width less than 10ns.
- 2. VTERM must not exceed Vcc + 10%.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range^(1,4) (Vcc = 5.0V ± 10%)

10111	por a tar o ar i	а сарргу ч	vortage rang	0 (00	C - 5.C	, v <u>-</u>	1070)						
									7142	1X20 1X20 Only	7142 Co	1X25 1X25 m'l Ind	
Symbol	Parameter		Test Condition		Versi	on	Тур.	Мах.	Тур.	Max.	Unit		
Icc	Dynamic Operating Current (Both Ports Active)	CEL and CER = VIL, Outputs Disabled f = fMax ⁽²⁾			COM'L	SA LA	110 110	250 200	110 110	220 170	mA		
			IND	SA LA	_	_	110 110	270 220					
ISB1	Standby Current (Both Ports - TTL Level Inputs)	$f = f(AX^{(2)})$	COM'L	SA LA	30 30	65 45	30 30	65 45	mA				
	Lever inpuis)		IND	SA LA			30 30	75 55					
ISB2	Standby Current (One Port - TTL	Active Port Outputs Disabled,	COM'L	SA LA	65 65	165 125	65 65	150 115	mA				
	Level Inputs)	f=fmax ⁽²⁾			IND	SA LA			65 65	170 140			
ISB3	Full Standby Current (Both Ports - CMOS Level Inputs)	CEL and CER ≥ Vcc - 0.2V,			COM'L	SA LA	1.0 0.2	15 5	1.0 0.2	15 5	mA		
	CMOS Level inputs)	$V_{IN} \ge V_{CC} - 0.2V$ or $V_{IN} \le 0.2V$, $f = 0^{(S)}$	IND	SA LA			1.0 0.2	30 10					
ISB4	(One Port - $\overline{CE}_{B''} > V_{CC} - 0.2V^{(5)}$		COM'L	SA LA	60 60	155 115	60 60	145 105	mA				
CMOS Level Inputs) $ \begin{array}{l} V_{\text{IN}} \geq \overline{V} \text{cc} - 0.2 V \text{ or } V_{\text{IN}} \leq 0.2 V \\ \text{Active Port Outputs Disabled,} \\ f = f_{\text{MAX}}^{(2)} \\ \end{array} $		IND	SA LA	_	_	60 60	165 130						

2691 tbl 04a

						7142	1X35 1X35 Only	7142 Co	1X55 1X55 m'l Ind	
	Symbol	Parameter	Test Condition	Versi	on	Тур.	Max.	Тур.	Max.	Unit
	Icc	Dynamic Operating Current (Both Ports Active)	CEL and CER = VIL, Outputs Disabled f = ftmx(2)	COM'L	SA LA	80 80	165 120	65 65	155 110	mA
	(Douit rous Active) I = MAX**	IND	SA LA			65 65	190 140			
	ISB1	Standby Current (Both Ports - TTL	oth Ports - TTL f = fivax ⁽²⁾ evel Inputs)	COM'L	SA LA	25 25	65 45	20 20	65 35	mA
	Level Inputs)	Lever inputs)		IND	SA LA			20 20	70 50	
	ISB2	Standby Current (One Port - TTL	CEA = VIL and CEB = VIH(5) Active Port Outputs Disabled,	COM'L	SA LA	50 50	125 90	40 40	110 75	mA
		Level Inputs)	f=fmax ⁽²⁾	IND	SA LA			40 40	125 90	
	ISB3	Full Standby Current (Both Ports - CMOS Level Inputs)	CE and CER ≥ Vcc - 0.2V,	COM'L	SA LA	1.0 0.2	15 4	1.0 0.2	15 4	mA
		Civios Level inpuis)) $V_{IN} \ge V_{CC} - 0.2V$ or $V_{IN} \le 0.2V$, $f = 0^{(S)}$	IND	SA LA			1.0 0.2	30 10	
	ISB4	(One Port - $\overline{CE}_{B''} \ge Vcc - 0.2V^{(5)}$	COM'L	SA LA	45 45	110 85	40 40	100 70	mA	
ČMOS Level Inputs)	$\begin{split} & \text{VIN} \geq \overline{\text{V}}\text{Cc} \cdot 0.2 \text{V or VIN} \leq 0.2 \text{V} \\ & \text{Active Port Outputs Disabled,} \\ & f = f_{\text{MAX}}^{(2)} \end{split}$	IND	SA LA			40 40	110 85			

NOTES:

2691 tbl 04b

- 1. 'X' in part numbers indicates power rating (SA or LA).
- 2. At f = fmax, address and control lines (except Output Enable) are cycling at the maximum frequency read cycle of 1/trc, and using "AC TEST CONDITIONS" of input levels of GND to 3V.
- 3. f = 0 means no address or control lines change. Applies only to inputs at CMOS level standby.
- 4. Vcc = 5V, Ta=+25°C for Typ and is not production tested. $Vcc \ DC = 100mA$ (Typ)
- 5. Port "A" may be either left or right port. Port "B" is opposite from port "A".

2691 tbl 05

2691 tbl 06

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range ($Vcc = 5.0V \pm 10\%$)

			71321SA 71421SA		71321LA 71421LA		
Symbol	Parameter	Test Conditions	Min.	Max.	Min.	Max.	Unit
ILI	Input Leakage Current ⁽¹⁾	Vcc = 5.5V, $Vin = 0V$ to Vcc	_	10	ı	5	μA
Ito	Output Leakage Current ⁽¹⁾	$\overline{\overline{CE}}$ = VIH, VOUT = 0V to VCC, VCC - 5.5V	_	10		5	μΑ
Vol	Output Low Voltage (I/Oo-I/O7)	IoL = 4mA	_	0.4	_	0.4	V
Vol	Open Drain O <u>utput</u> Low Voltage (BUSY/INT)	loL = 16mA	_	0.5	ĺ	0.5	V
Voh	Output High Voltage	IOH = -4mA	2.4	1	2.4	_	V

NOTE:

1. At $Vcc \le 2.0V$ leakages are undefined.

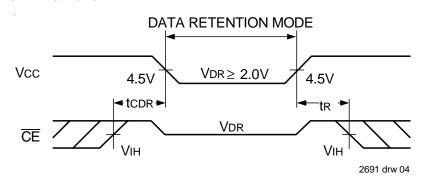
Data Retention Characteristics (LA Version Only)

Symbol	Parameter	Test Condition		Min.	Typ. ⁽¹⁾	Max.	Unit
VDR	Vcc for Data Retention			2.0	_	0	V
ICCDR	Data Retention Current	Vcc = 2.0V, CE ≥ Vcc - 0.2V	COM'L		100	1500	μA
		$Vin \ge Vcc - 0.2V$ or $Vin \le 0.2V$	IND	_	100	4000	μΑ
tcdr(3)	Chip Deselect to Data Retention Time			0	_	_	ns
tR ⁽³⁾	Operation Recovery Time			trc ⁽²⁾	_		ns

NOTES:

- 1. Vcc = 2V, TA = +25°C, and is not production tested.
- 2. trc = Read Cycle Time
- 3. This parameter is guaranteed but not production tested.

Data Retention Waveform



AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	5ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1,2 and 3

2691 tbl 07

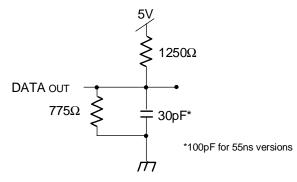


Figure 1. AC Output Test Load

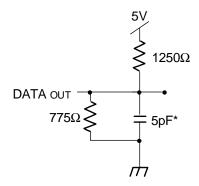
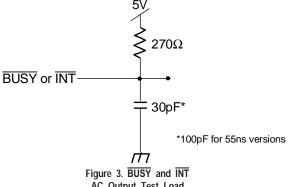


Figure 2. Output Test Load (for thz, tLz, twz, and tow) * Including scope and jig.



AC Output Test Load

2691 drw 05

AC Electrical Characteristics Over the Operating Temperature Supply Voltage Range⁽²⁾

		71321X20 71421X20 Com'l Only		71321X25 71421X25 Com'l & Ind		
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
READ CYCLE						
trc	Read Cycle Time	20	1	25		ns
taa	Address Access Time	_	20	1	25	ns
tace	Chip Enable Access Time		20	ı	25	ns
taoe	Output Enable Access Time	_	11	-	12	ns
tон	Output Hold from Address Change	3	_	3	_	ns
tLz	Output Low-Z Time ^(1,3)	0	1	0		ns
tHZ	Output High-Z Time ^(1,3)	_	10	_	10	ns
tpu	Chip Enable to Power Up Time (5)	0	_	0	_	ns
tPD	Chip Disable to Power Down Time ⁽³⁾	_	20	_	25	ns

2691 tbl 08a

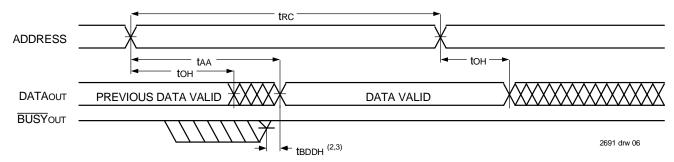
		7142	71321X35 71421X35 Com'l Only		71321X55 71421X55 Com'l & Ind				
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit			
READ CYCLE									
trc	Read Cycle Time	35	1	55	_	ns			
taa	Address Access Time	-	35		55	ns			
tace	Chip Enable Access Time	-	35		55	ns			
taoe	Output Enable Access Time	_	20	_	25	ns			
tон	Output Hold from Address Change	3	_	3	_	ns			
tLZ	Output Low-Z Time ^(1,3)	0	-	5	_	ns			
tHZ	Output High-Z Time ^(1,3)	_	15	_	25	ns			
ten	Chip Enable to Power Up Time ⁽³⁾	0	_	0	_	ns			
t₽D	Chip Disable to Power Down Time ⁽³⁾		35		50	ns			

NOTES:

- 1. Transition is measured 0mV from Low or High-impedance voltage Output Test Load (Figure 2).
- 2. 'X' in part numbers indicates power rating (SA or LA).
- 3. This parameter is guaranteed by device characterization, but is not production tested.

2691 tbl 08b

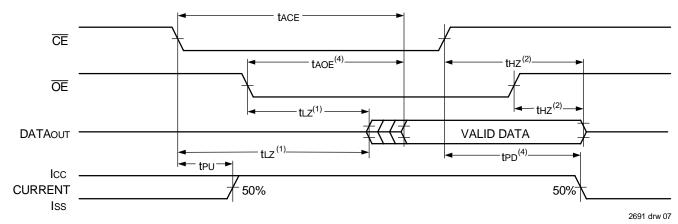
Timing Waveform of Read Cycle No. 1, Either Side⁽¹⁾



NOTES:

- 1. $R\overline{W} = V_{IH}$, $\overline{CE} = V_{IL}$, and is $\overline{OE} = V_{IL}$. Address is valid prior to the coincidental with \overline{CE} transition LOW.
- 2. tbdd delay is required only in the case where the opposite port is completing a write operation to the same address location. For simultaneous read operations BUSY has no relationship to valid output data.
- 3. Start of valid data depends on which timing becomes effective last tAOE, tACE, tAA, and tBDD.

Timing Waveform of Read Cycle No. 2, Either Side (3)



NOTES:

- 1. Timing depends on which signal is asserted last, $\overline{\text{OE}}$ or $\overline{\text{CE}}$.
- 2. Timing depends on which signal is de-asserted first, $\overline{\text{OE}}$ or $\overline{\text{CE}}$.
- 3. $R\overline{W} = VIH$ and $\overline{OE} = VIL$, and the address is valid prior to or coincidental with \overline{CE} transition LOW.
- 4. Start of valid data depends on which timing becomes effective last tage, ta

AC Electrical Characteristics Over the Operating Temeprature and Supply Voltage Range⁽⁴⁾

		71321X20 71421X20 Com'l Only		71321X25 71421X25 Com'l & Ind		
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
WRITE CYCLE						
twc	Write Cycle Time ⁽²⁾	20	_	25	_	ns
tew	Chip Enable to End-of-Write	15	-	20		ns
taw	Address Valid to End-of-Write	15	-	20	-	ns
tas	Address Set-up Time	0	-	0		ns
twp	Write Pulse Width ⁽³⁾	15	-	15	ı	ns
twr	Write Recovery Time	0	1	0	1	ns
tow	Data Valid to End-of-Write	10		12		ns
tHZ	Output High-Z Time ⁽¹⁾	-	10	_	10	ns
tон	Data Hold Time	0	_	0		ns
twz	Write Enable to Output in High-Z ⁽¹⁾	_	10	_	10	ns
tow	Output Active from End-of-Write ⁽¹⁾	0		0		ns

2691 tbl 09a

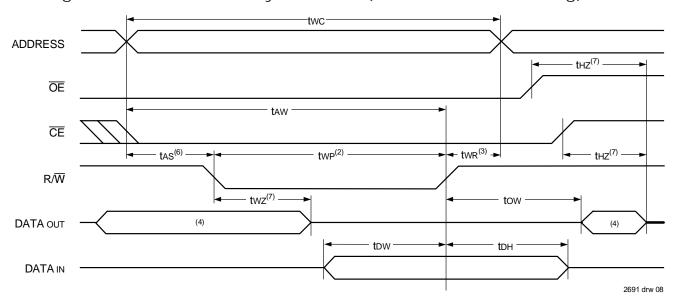
		7142	1X35 1X35 I Only	71321X55 71421X55 Com'l & Ind			
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit	
WRITE CYCLE							
twc	Write Cycle Time ⁽²⁾	35		55	_	ns	
tew	Chip Enable to End-of-Write	30	1	40	_	ns	
taw	Address Valid to End-of-Write	30	-	40		ns	
tas	Address Set-up Time	0		0	_	ns	
twp	Write Pulse Width ⁽³⁾	25	1	30	_	ns	
twr	Write Recovery Time	0		0		ns	
tow	Data Valid to End-of-Write	15	1	20	_	ns	
tHZ	Output High-Z Time ⁽¹⁾	-	15	_	25	ns	
тон	Data Hold Time	0	-	0	_	ns	
twz	Write Enable to Output in High-Z ⁽¹⁾	_	15	_	30	ns	
tow	Output Active from End-of-Write ⁽¹⁾	0	_	0		ns	

NOTES:

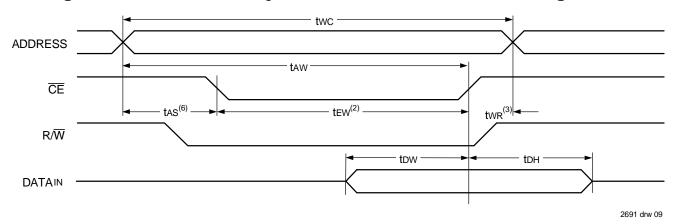
2691 tbl 09b

- Transition is measured 0mV from Low or High-impedance voltage with Output Test Load (Figure 2). This parameter is guaranteed by device characterization but is not production tested.
- 2. For Master/Slave combination, two = tbaa + twp, since R/\overline{W} = V_{IL} must occur after tbaa .
- 3. If \overline{OE} is LOW during a R/ \overline{W} controlled write cycle, the write pulse width must be the larger of twp or (twz + tow) to allow the I/O drivers to turn off data to be placed on the bus for the required tow. If \overline{OE} is HIGH during a R/ \overline{W} controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.
- 4. 'X' in part numbers indicates power rating (SA or LA).

Timing Waveform of Write Cycle No. 1, (R/W Controlled Timing)(1,5,8)



Timing Waveform of Write Cycle No. 2, (**CE** Controlled Timing)^(1,5)



NOTES:

- 1. $R\overline{W}$ or \overline{CE} must be HIGH during all address transitions.
- 2. A write occurs during the overlap (tew or twp) of \overline{CE} = V_{IL} and R/W= V_{IL}.
- 3. twn is measured from the earlier of $\overline{\text{CE}}$ or R/\overline{W} going HIGH to the end of the write cycle.
- 4. During this period, the I/O pins are in the output state and input signals must not be applied.
- 5. If the CE LOW transition occurs simultaneously with or after the RW LOW transition, the outputs remain in the High-impedance state.
- 6. Timing depends on which enable signal (CE or R/W) is asserted last.
- 7. This parameter is determined to be device characterization, but is not production tested. Transition is measured 0mV from steady state with the Output Test Load (Figure 2).
- 8. If \overline{OE} is LOW during a R \overline{W} controlled write cycle, the write pulse width must be the larger of twp or (twz + tow) to allow the I/O drivers to turn off data to be placed on the bus for the required tow. If \overline{OE} is HIGH during a R \overline{W} controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽⁶⁾

	71321X20 71421X20 Com'l Only						
Symbol	Parameter	Min.	Мах.	Min.	Max.	Unit	
BUSY TIMING	(For MASTER 71321)						
t BAA	BUSY Access Time from Address		20	-	20	ns	
t BDA	BUSY Disable Time from Address	-	20		20	ns	
t BAC	BUSY Access Time from Chip Enable	-	20		20	ns	
tBDC	BUSY Disable Time from Chip Enable	_	20	_	20	ns	
twn	Write Hold After BUSY ⁽⁵⁾	12	_	15	-	ns	
twdd	Write Pulse to Data Delay ⁽¹⁾	_	50	_	50	ns	
tood	Write Data Valid to Read Data Delay ⁽¹⁾	-	35	_	35	ns	
taps	Arbitration Priority Set-up Time ⁽²⁾	5	_	5	-	ns	
tBDD	BUSY Disable to Valid Data ⁽³⁾		25	_	35	ns	
BUSY INPUT TIMING (For SLAVE 71421)							
twB	Write to BUSY Input ⁽⁴⁾	0		0		ns	
twn	Write Hold After BUSY ⁽⁵⁾	12	_	15	_	ns	
twdd	Write Pulse to Data Delay ⁽¹⁾		40	_	50	ns	
tood	Write Data Valid to Read Data Delay ⁽¹⁾		30	_	35	ns	

2691 tbl 10a

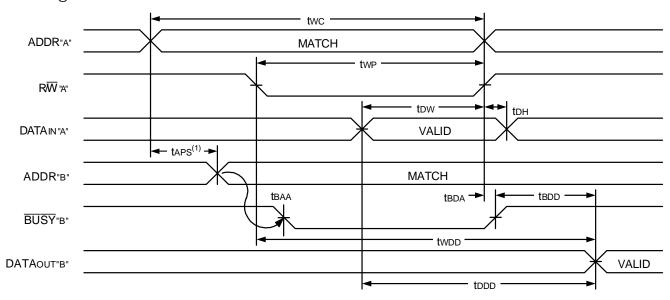
		7142	71321X35 71321X55 71421X35 71421X55 Com'l Only Com'l & Ind			
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
BUS Y TIMING	(For MASTER 71321)					
tbaa	BUSY Access Time from Address	-	20	_	30	ns
tBDA	BUSY Disable Time from Address		20	-	30	ns
t BAC	BUSY Access Time from Chip Enable		20	-	30	ns
tBDC	BUSY Disable Time from Chip Enable		20	_	30	ns
twн	Write Hold After BUSY ⁽⁵⁾	20	-	20		ns
twdd	Write Pulse to Data Delay ⁽¹⁾	_	60	_	80	ns
tood	Write Data Valid to Read Data Delay ⁽¹⁾		35	_	55	ns
taps	Arbitration Priority Set-up Time ⁽²⁾	5	-	5	-	ns
tBDD	BUSY Disable to Valid Data ⁽³⁾		35		50	ns
BUSY INPUT 1	IMING (For SLAVE 71421)					
twB	Write to BUSY Input ⁴⁾	0	-	0	-	ns
twн	Write Hold After BUSY ⁽⁵⁾	20	_	20	_	ns
twdd	Write Pulse to Data Delay ⁽¹⁾		60	_	80	ns
tooo	Write Data Valid to Read Data Delay ⁽¹⁾	_	35	_	55	ns

NOTES

- 1. Port-to-port delay through RAM cells from the writing port to the reading port, refer to "Timing Waveform of Write with Port-to-Port Read and BUSY."
- 2. To ensure that the earlier of the two ports wins.
- 3. tbdd is a calculated parameter and is the greater of 0, twdd twp (actual) or tddd tdw (actual).
- 4. To ensure that a write cycle is inhibited on port "B" during contention on port "A".
- 5. To ensure that a write cycle is completed on port "B" after contention on port "A".
- 6. 'X' in part numbers indicates power rating (SA or LA)..

2691 tbl 10b

Timing Waveform of Write with Port-to-Port Read and **BUSY**(2,3,4)

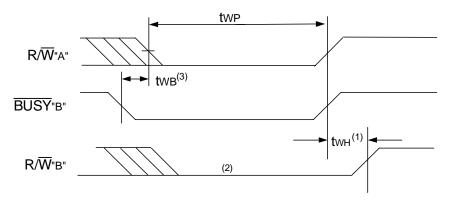


NOTES:

2691 drw 10

- 1. To ensure that the earlier of the two ports wins. taps is ignored for Slave (IDT71421).
- 2. $\overline{CE}L = \overline{CE}R = VIL$
- 3. \overline{OE} = V_{IL} for the reading port.
- 4. All timing is the same for the left and right ports. Port "A" may be either the left or right port. Port "B" is opposite from port "A".

Timing Waveform of Write with **BUSY**(4)

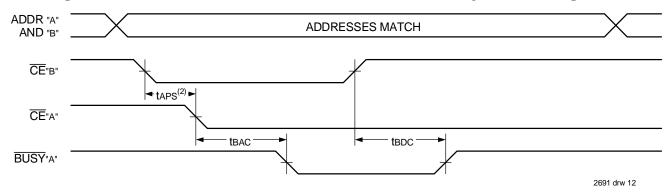


NOTES:

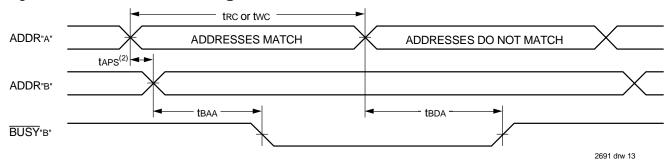
2691 drw 11

- 1. $\underline{\text{tw}}\underline{\text{m}}\underline{\text{m}}$ be met for both $\overline{\text{BUSY}}$ input (IDT71421, slave) or output (IDT71321, Master).
- 2. BUSY is asserted on port "B" blocking R/W"B", until BUSY"B" goes HIGH.
- 3. twb is only for the slave version (IDT71421).
- 4. All timing is the same for the left and right ports. Port "A" may be either the left or right port. Port "B" is opposite from port "A".

Timing Waveform of **BUSY** Arbitration Controlled by **CE** Timing⁽¹⁾



Timing Waveform of $\overline{\textbf{BUSY}}$ Arbritration Controlled by Address Match Timing $^{(1)}$



NOTES:

- 1. All timing is the same for left and right ports. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 2. If taps is not satisfied, the BUSY will be asserted on one side or the other, but there is no guarantee on which side BUSY will be asserted (IDT71321 only).

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽¹⁾

		7142	1X20 1X20 Only	7132 7142 Co &		
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
INTERRUPT T	MING					
tas	Address Set-up Time	0	_	0	_	ns
twr	Write Recovery Time	0	-	0		ns
tins	Interrupt Set Time	_	20		25	ns
tinr	Interrupt Reset Time	_	20	_	25	ns

NOTES

1. 'X' in part numbers indicates power rating (SA or LA).

2691 tbl 11 a

AC Electrical Characteristics Over the Operating Temperature Supply Voltage Range⁽¹⁾

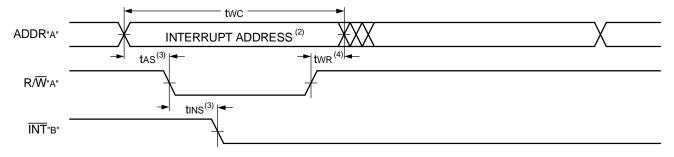
		7142	1X35 1X35 Only	7132 7142 Co &		
Symbol	Parameter	Min.	Max.	Unit		
INTERRUPT 1	TIMING					
tas	Address Set-up Time	0	_	0	_	ns
twr	Write Recovery Time	0	_	0	_	ns
tins	Interrupt Set Time	_	25	_	45	ns
tinr	Interrupt Reset Time	_	25		45	ns

NOTES:

1. 'X' in part numbers indicates power rating (SA or LA).

Timing Waveform of Interrupt Mode⁽¹⁾

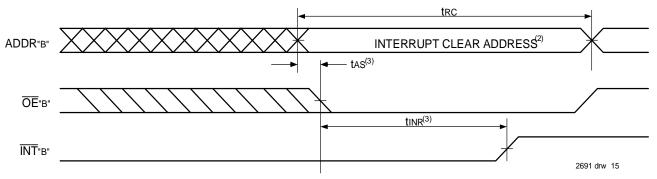
SET **INT**



2691 drw 14

2691 tbl 11b

CLEAR **INT**



- 1. All timing is the same for left and right ports. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 2. See Interrupt Truth Table.
- Timing depends on which enable signal (CE or RW) is asserted last.
 Timing depends on which enable signal (CE or RW) is de-asserted first.

2691 thl 13

Truth Tables

Truth Table I. Non-Contention Read/Write Control⁽⁴⁾

Left or Right Port ⁽¹⁾				
R/W	CE	Œ	D ₀₋₇	Function
Х	Н	Х	Z	Port Disabled and in Power-Down Mode, ISB2 or ISB4
Х	Н	Х	Z	CER = CEL = VH, Power-Down Mode, ISB1 or ISB3
L	L	Х	DATAIN	Data on Port Written Into Memory ⁽²⁾
Н	L	L	DATAоит	Data in Memory Output on Port ⁽³⁾
Н	L	Н	Z	High Impedance Outputs

NOTES: 2691 tbl 12

- 1. AOL A10L \neq A0R A10R.
- 2. If $\overline{\text{BUSY}} = \text{L}$, data is not written.
- 3. If $\overline{BUSY} = L$, data may not be valid, see two and too timing.
- 4. 'H' = VIH, 'L' = VIL, 'X' = DON'T CARE, 'Z' = HIGH IMPEDANCE

Truth Table II. Interrupt Flag^(1,4)

Left Port							Right Por	t		
R/WL	ĒĒ⊥	ŌĒL	A10L-A0L	ΪΝΤ̈́L	R/W̄R	CER	ŌĒR	A10R-A0R	Ī NT R	Function
L	L	Х	7FF	Х	Х	Х	Х	Х	L ⁽²⁾	Set Right INTR Flag
Х	Х	Х	Х	Х	Х	L	L	7FF	H ⁽³⁾	Reset Right INTR Flag
Х	Х	Х	Х	L ⁽³⁾	L	L	Х	7FE	Х	Set Left INTL Flag
Х	L	L	7FE	H ⁽²⁾	Х	Х	Х	Х	Х	Reset Left INTL Flag

NOTES:

- 1. Assumes $\overline{BUSY}_L = \overline{BUSY}_R = V_{IH}$
- 2. If $\overline{BUSY}_L = V_{IL}$, then No Change.
- 3. If $\overline{\text{BUSYR}} = \text{VIL}$, then No Change.
- 4. 'H' = HIGH, 'L' = LOW, 'X' = DON'T CARE

Truth Table III — Address **BUSY** Arbitration

	In	puts	Out	puts	
CEL	CE _R	Aol-A1ol Aor-A1or	BUS YL(1)	BUSY _R (1)	Function
Х	Х	NO MATCH	Н	Н	Normal
Н	Х	MATCH	Н	Н	Normal
Х	Н	MATCH	Н	Н	Normal
L	L	MATCH	(2)	(2)	Write Inhibit ⁽³⁾

NOTES:

2691 tbl 14

- 1. Pins BUSYL and BUSYR are both outputs for IDT71321 (Master). Both are inputs for IDT71421 (Slave). BUSYx outputs on the IDT71321 are open drain, not pushpull outputs. On slaves the BUSYx input internally inhibits writes.
- 2. 'L' if the inputs to the opposite port were stable prior to the address and enable inputs of this port. 'H' if the inputs to the opposite port became stable after the address and enable inputs of this port. If taps is not met, either BUSY_L or BUSY_R = LOW will result. BUSY_L and BUSY_R outputs can not be LOW simultaneously.
- 3. Writes to the left port are internally ignored when BUSYL outputs are driving LOW regardless of actual logic level on the pin. Writes to the right port are internally ignored when BUSYR outputs are driving LOW regardless of actual logic level on the pin.

Functional Description

The IDT71321/IDT71421 provides two ports with separate control, address and I/O pins that permit independent access for reads or writes to any location in memory. The IDT71321/IDT71421 has an automatic power down feature controlled by $\overline{\text{CE}}$. The $\overline{\text{CE}}$ controls on-chip power down circuitry that permits the respective port to go into a standby mode when not selected ($\overline{\text{CE}}$ = V_{I+}). When a port is enabled, access to the entire memory array is permitted.

Interrupts

If the user chooses the interrupt function, a memory location (mail box or message center) is assigned to each port. The left port interrupt flag ($\overline{\text{INT}}_L$) is asserted when the right port writes to memory location 7FE (HEX), where a write is defined as the $\overline{\text{CE}}_R = R/\overline{W}_R = V_{IL}$, per Truth Table II. The left port clears the interrupt by accessing address location 7FE when $\overline{\text{CE}}_L = \overline{\text{OE}}_L = V_{IL}$, R/W is a "don't care". Likewise, the right port interrupt flag ($\overline{\text{INT}}_R$) is asserted when the left port writes to memory location 7FF (HEX) and to clear the interrupt flag ($\overline{\text{INT}}_R$), the right port must access the memory location 7FF. The message (8 bits) at 7FE or 7FF is user-defined, since it is an addressable SRAMlocation. If the interrupt function is not used, address locations 7FE and 7FF are not used as mail boxes, but as part of the random access memory. Refer to Truth Table II for the interrupt operation.

Busy Logic

Busy Logic provides a hardware indication that both ports of the RAM have accessed the same location at the same time. It also allows one of the two accesses to proceed and signals the other side that the RAM is "Busy". The $\overline{\text{BUSY}}$ pin can then be used to stall the access until the operation on the other side is completed. If a write operation has been attempted from the side that receives a busy indication, the write signal is gated internally to prevent the write from proceeding.

The use of \overline{BUSY} Logic is not required or desirable for all applications. In some cases it may be useful to logically OR the \overline{BUSY} outputs together and use any \overline{BUSY} indication as an interrupt source to flag the event of an illegal or illogical operation. In slave mode the \overline{BUSY} pin operates solely as a write inhibit input pin. Normal operation can be programmed by tying the \overline{BUSY} pins HIGH. If desired, unintended write operations can be prevented to a port by tying the \overline{BUSY} pin for that port LOW.

The BUSY outputs on the IDT71321 (Master) are open drain type outputs and require open drain resistors to operate. If these SRAMs are

being expanded in depth, then the BUSY indication for the resulting array does not require the use of an external AND gate.

Width Expansion with Busy Logic Master/Slave Arrays

When expanding an SRAM array in width while using \overline{BUSY} logic, one master part is used to decide which side of the SRAM array will receive a \overline{BUSY} indication, and to output that indication. Any number of slaves to be addressed in the same address range as the master, use the \overline{BUSY} signal as a write inhibit signal. Thus on the IDT71321/IDT71421 SRAMs the \overline{BUSY} pin is an output if the part is Master (IDT71321), and the \overline{BUSY} pin is an input if the part is a Slave (IDT71421) as shown in Figure 3.

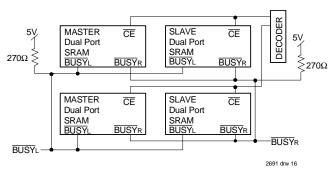
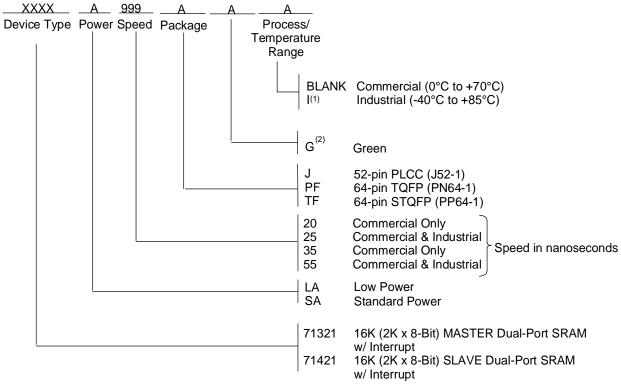


Figure 3. Busy and chip enable routing for both width and depth expansion with IDT71321 (Master) and (Slave) IDT71421 SRAMs.

If two or more master parts were used when expanding in width, a split decision could result with one master indicating BUSY on one side of the array and another master indicating BUSY on one other side of the array. This would inhibit the write operations from one port for part of a word and inhibit the write operations from the other port for the other part of the word.

The \overline{BUSY} arbitration, on a Master, is based on the chip enable and address signals only. It ignores whether an access is a read or write. In a master/slave array, both address and chip enable must be valid long enough for a \overline{BUSY} flag to be output from the master before the actual write pulse can be initiated with either the R/\overline{W} signal or the byte enables. Failure to observe this timing can result in a glitched internal write inhibit signal and corrupted data in the slave.

Ordering Information



NOTES: 2691 drw 17

- 1. Contact your sales office for industrial temperature range availability in other speeds, packages and powers.
- 2. Green parts available. For specific speeds, packages and powers contact your local sales office.

Datasheet Document History

03/24/99:		Initiated datasheet document history
		Converted to new format
		Cosmetic typographical corrections
	Pages 2 and 3	Added additional notes to pin configurations
06/07/99:		Changed drawing format Changed drawing for Changed drawing format Changed drawing for Ch
11/10/99:		Replaced IDT logo
08/23/01:	Page 3	Increased storage temperature parameters
		Clarified TA parameter
	Page 4	DC Electrical parameters-changed wording from "open" to "disabled"
	Page 16	Fixed part numbers in "Width Expansion" paragraph
		Changed ±500mV to 0mV in notes
	Page 4	Industrial temperature range offering added to DC Electrical Characteristisc for 25ns and removed for
		35ns
	Page 7 and 9	Industrial temperature range added to AC Electrical Characteristics for 25ns
	Page 17	Industrial offering removed for 35ns ordering information
01/17/06:	Page 1	Added green availability to features
	Page 17	Added green indicator to ordering information
	Page 1 & 17	Replaced old IDT™ with new IDT™ logo
08/25/06:	Page 14	Changed INT"A" to INT"B" in the CLEAR INT drawing in the Timing Waveform of Interrupt Mode
10/29/08:	Page 17	Removed "IDT" from orderable part number



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